

DESCRIPTION

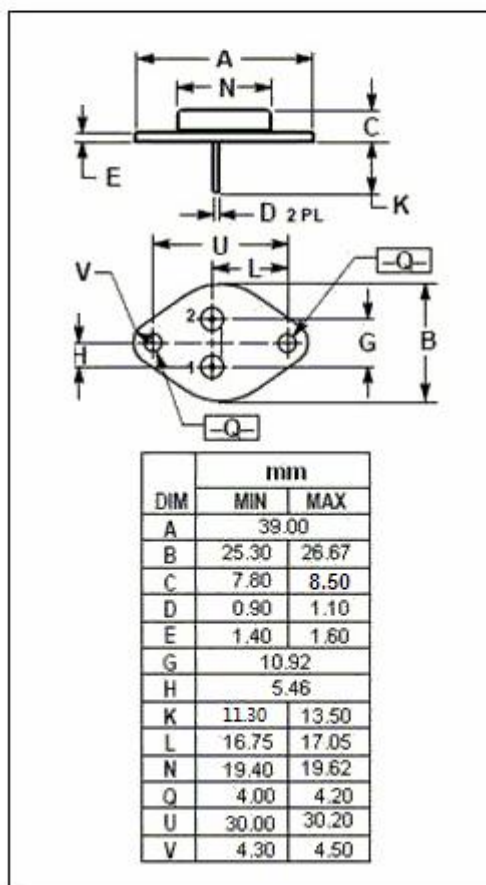
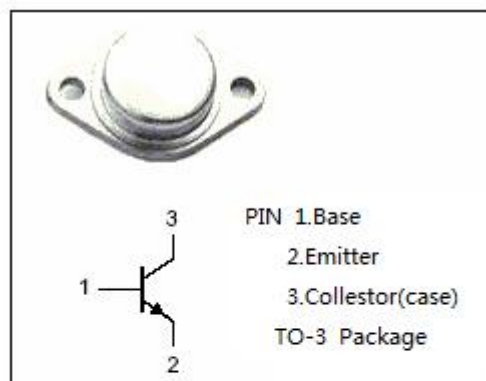
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V$ (Min)
- Wide Area of Safe Operation
- High Current Capability

APPLICATIONS

- Designed for AF high power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ C$)

SYMBOL	PARAMETER	MAX	UNIT
V_{CBO}	Collector-Base Voltage	110	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	15	A
I_{CM}	Collector Current-Peak	30	A
P_C	Collector Power Dissipation @ $T_C=25^\circ C$	100	W
T_j	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-65~150	$^\circ C$



SPTECH Silicon NPN Power Transistor**2SD750****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 10mA; I _B = 0	80			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E =1mA; I _C = 0	7			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 5A; I _B = 0.5A			2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 5A; V _{CE} = 4V			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 40V; I _E = 0			30	μA
h _{FE-1}	DC Current Gain	I _C = 1A; V _{CE} = 4V	40			
h _{FE-2}	DC Current Gain	I _C = 5A; V _{CE} = 4V	30		120	
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 10V		1		MHz

◆ **h_{FE-2} Classifications**

Q	P	O
30-60	40-80	60-120